

NPN SILICON RF MICROWAVE TRANSISTOR

DESCRIPTION:

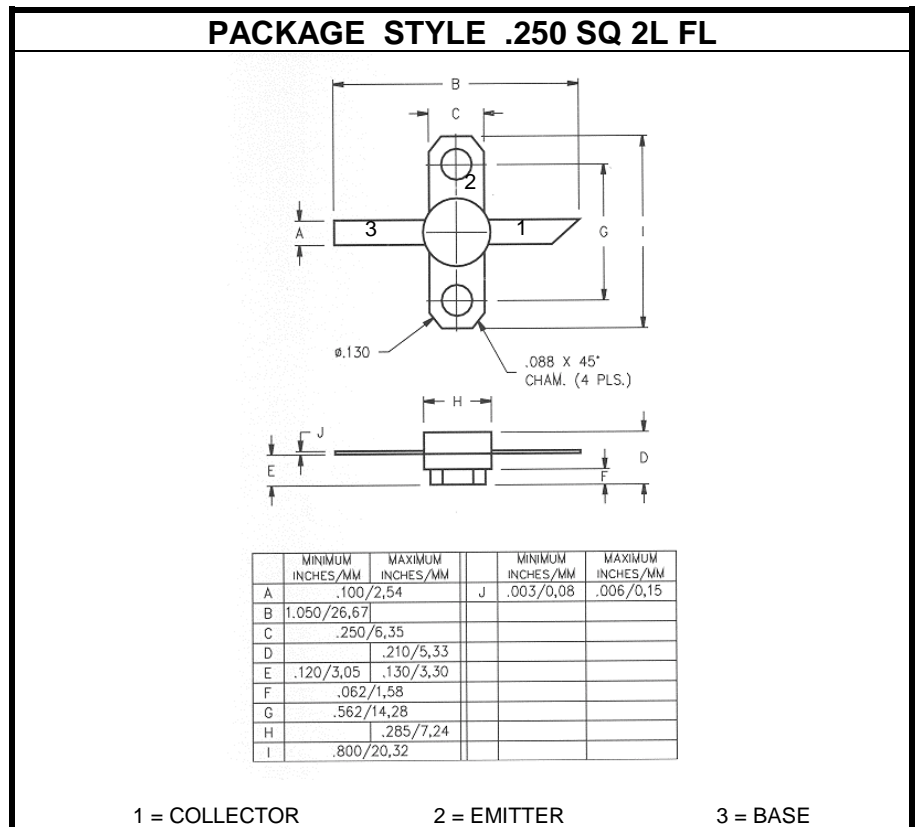
The **ASI MSC1004M** is low level Class-C, Common Base Device Designed for IFF, DME driver Applications.

FEATURES INCLUDE:

- Gold Metalization
- Input Matching
- Emitter Ballasting

MAXIMUM RATINGS

I_C	650 mA
V_{CC}	32 V
P_{DISS}	18 W @ T _C ≤ 100 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	5.0 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 1.0 mA	45			
BV_{CER}	I _C = 25 mA R _{BE} = 10 Ω	45			V
BV_{EBO}	I _E = 1.0 mA	3.5			V
I_{CES}	V _{CE} = 28 V			1.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 200 mA	30		300	
P_G	V _{CE} = 28 V P _{IN} = 500 mW f = 1025 to 1150 MHz PULSE WIDTH = 10 μS DUTY CYCLE = 1.0%	9.0			dB
P_{OUT}		4.0			W
η		35			%